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(71) Applicant (for all designated States except US): **APPLIED MATERIALS, INC.** [US/US]; P.O. Box 450A, Santa Clara, California 95052 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **YUAN, Zheng** [CA/US]; 42024 Benbow Dr., Fremont, California 94539 (US). **VENKATARAMAN, Shankar** [IN/US]; 2444 Notre Dame Dr., Santa Clara, California 95051 (US). **CHING, Cary** [US/US]; 948 E. Cardinal Dr., Sunnyvale, California 94087 (US). **WONG, Shan** [US/US]; 19500

Pruneridge Ave., Apt. 6302, Cupertino, California 95014 (US). **MUKAI, Kevin, Mikio** [US/US]; 2012 Cabrillo Ct., Santa Clara, California 95051 (US). **INGLE, Nitin, K.** [IN/US]; 999 W. Hamilton Ave., #97, Campbell, California 95008 (US).

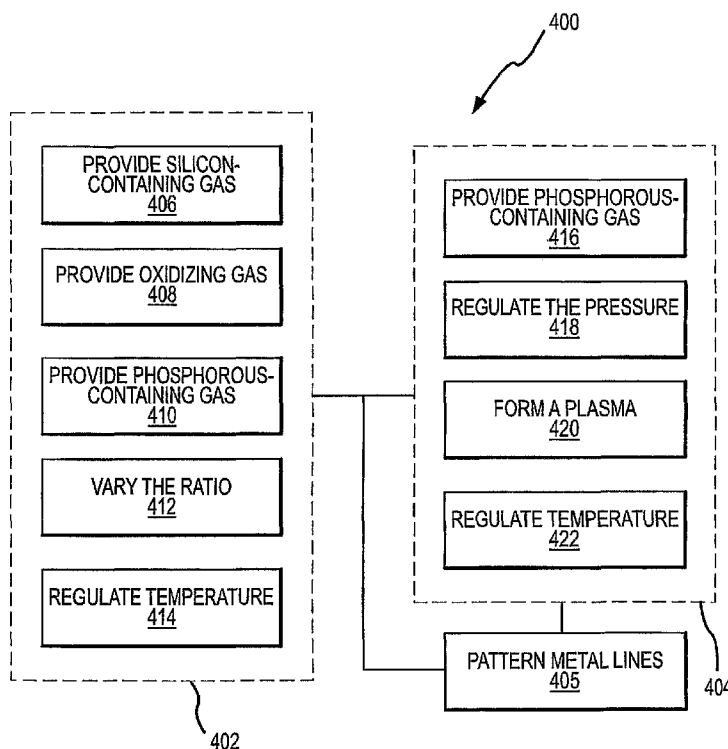
(74) Agent: **BRANCH, Irwin, E.**; Townsend and Townsend and Crew LLP, Two Embarcadero Center, Eighth Floor, San Francisco, California 94111-3834 (US).

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(54) Title: LIMITED THERMAL BUDGET FORMATION OF PMD LAYERS



(57) Abstract: A method of filling a gap which is defined by adjacent raised features on a substrate includes providing a flow of a silicon-containing processing gas to a chamber housing the substrate, providing a flow of an oxidizing processing gas to the chamber, and providing a flow of a phosphorous-containing processing gas to the chamber. The method also includes depositing a first portion of a P-doped silicon oxide film as a substantially conformal layer in the gap by causing a reaction between the silicon-containing processing gas, the phosphorous-containing processing gas, and the oxidizing processing gas. Depositing the conformal layer includes varying over time a ratio of the (silicon-containing processing gas):(oxidizing processing gas) and maintaining the temperature of the substrate below about 500°C throughout deposition of the conformal layer. The method also includes depositing a second portion of the P-doped silicon oxide film as a bulk layer. Depositing a second portion of the film includes maintaining the ratio of the (silicon-containing processing gas plus phosphorous-containing processing gas):(oxidizing processing gas) substantially

constant throughout deposition of the bulk layer and maintaining the temperature of the substrate below about 500°C throughout deposition of the bulk layer.



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